

ABSTRACT OF THE DISCLOSURE

A lateral semiconductor device includes an n-type buffer layer (15) selectively formed in the surface of an n-type base layer (14), a p-type drain layer (16) selectively
5 formed in the surface of the n-type buffer layer (15), a p-type base layer (17) formed in the surface of the n-type base layer (14) so as to surround the n-type buffer layer (15), an n⁺-type source layer (18) selectively formed in the surface of the p-type base layer (17), a source electrode (24) in contact
10 with the p-type base layer (17) and the n⁺-type source layer (18), a drain electrode (22) in contact with the p-type drain layer (16), and a gate electrode (20) formed via a gate insulating film (19) on the surface of the p-type base layer (17) sandwiched between the n⁺-type source layer (18) and the
15 n-type base layer (14). The p-type drain layer (16) has an annular structure or horseshoe-shaped structure, or is divided into a plurality of portions. This realizes a high breakdown voltage with a low ON voltage.